

Vishay Semiconductors

Single-Line ESD-Protection in SOT-23

ORDERING CODE

GSOT03-GS08

GSOT03-V-G-08 GSOT04-GS08

GSOT04-V-G-08

GSOT05-GS08

GSOT05-V-G-08

GSOT08-GS08

GSOT08-V-G-08

GSOT12-GS08

GSOT12-V-G-08

GSOT15-GS08

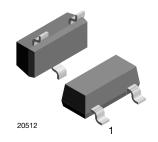
GSOT15-V-G-08

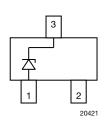
GSOT24-GS08

GSOT24-V-G-08

GSOT36-GS08

GSOT36-V-G-08





MARKING (example only)

DEVICE NAME

GSOT03

GSOT04

GSOT05

GSOT08

GSOT12

GSOT15

GSOT24

GSOT36



ENVIRONMENTAL

STATUS

Standard

Green

Standard

Green

Standard

Green

Standard

Green Standard

Green Standard

Green

Standard

Green

Standard

Green

YYY = type code (see table below) XX = date code

ORDERING INFORMATION

FEATURES

- Single-line ESD-protection device
- ESD-protection acc. IEC 61000-4-2

TAPED UNITS PER REEL

(8 mm TAPE ON 7" REEL)

3000

3000

3000

3000

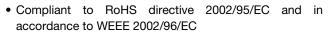
3000

3000

3000

3000

- ± 30 kV contact discharge
- ± 30 kV air discharge
- Space saving SOT-23 package
- AEC-Q101 qualified
- e3 Sn







GREEN



MINIMUM ORDER

QUANTITY

15 000

15 000

15 000

15 000

15 000

15 000

15 000

15 000

** Please see document "Vishay Material Category Policy": www.vishay.com/doc?99902

GSOT03 to GSOT36

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PACKA	GE DATA						
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS
000700		03	Standard	8.8 mg		MSL level 1	
GSOT03	SOT-23	03G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals
000704	007.00	04	Standard	8.8 mg		MSL level 1	200.00/40
GSOT04	SOT-23	04G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals
		05	Standard	8.8 mg		MSL level 1	
GSOT05	SOT-23	05G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals
000700		08	Standard	8.8 mg		MSL level 1	222.2011
GSOT08	SOT-23	08G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals
0007/0		12	Standard	8.8 mg		MSL level 1	
GSOT12	SOT-23	12G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals
000717		15	Standard	8.8 mg		MSL level 1	222.2011
GSOT15	SOT-23	15G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals
000704		24	Standard	8.8 mg		MSL level 1	222.2011
GSOT24	SOT-23	24G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals
000705	207.00	36	Standard	8.8 mg		MSL level 1	000 00 40
GSOT36	SOT-23	36G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	260 °C/10 s at terminals

ABSOLUTE MAXIMUM RATINGS GSOT03						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	30	Α		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	369	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV		
ESD IIIIIIdility	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV		
Operating temperature	Junction temperature	T_J	- 40 to + 125	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT04						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	30	Α		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 µs; single shot	P_{PP}	429	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
ESD illillidility	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		





Single-Line ESD-Protection in SOT-23

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ABSOLUTE MAXIMUM RATINGS GSOT05						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	30	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	480	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV		
E3D IIIIIIIIIIIII	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV		
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT08						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	18	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	345	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
ESD initiditity	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT12						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	I _{PPM}	12	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \mu s$; single shot	P _{PP}	312	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV		
E3D Illillidility	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV		
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		

ABSOLUTE MAXIMUN	ABSOLUTE MAXIMUM RATINGS GSOT15						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	8	Α			
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	230	W			
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV			
E3D Illillidility	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30 ± 30	kV			
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C			
Storage temperature		T _{STG}	- 55 to + 150	°C			

ABSOLUTE MAXIMUM RATINGS GSOT24						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	5	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	235	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		

Document Number: 85807 Rev. 2.0, 22-Jul-10 For technical questions, contact: ESDprotection@vishay.com

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Single-Line ESD-Protection in SOT-23



ABSOLUTE MAXIMUM RATINGS GSOT36						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	3.5	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	248	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV		
ESD Illillidility	Air discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	248 ± 30 ± 30	kV		
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C		
Storage temperature		T _{STG}	- 55 to + 150	°C		

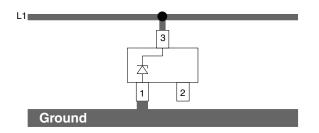
BIAs-MODE (1-line bidirectional asymmetrical protection mode)

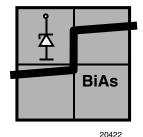
With the GSOTxx one signal- or data-lines (L1) can be protected against voltage transients. With pin 1 connected to ground and pin 3 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified maximum reverse working voltage (V_{RWM}) the protection diode between pin 1 and pin 3 offer a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the break through voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The clamping voltage (V_C) is defined by the breakthrough voltage (V_{BR}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection device.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction of the protection diode. The low forward voltage (V_F) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the GSOTxx clamping behaviour is bidirectional and asymmetrical (BiAs).





ELECTRICAL CHARACTERISTICS GSOT03							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines	
Reverse working voltage	at I _R = 100 μA	V_{RWM}	3.3	-	-	V	
Reverse current	at V _R = 3.3 V	I _R	-	-	100	μΑ	
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	4	4.6	-	V	
Payaraa alamaina valtaga	at I _{PP} = 1 A	\/	-	5.7	7.5	V	
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	10	12.3	V	
Converd elemening veltage	at I _{PP} = 1 A		=.	1	1.2	V	
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V	
Canacitanas	at V _R = 0 V; f = 1 MHz		-	420	600	pF	
Capacitance	at V _R = 1.6 V; f = 1 MHz	C _D	-	260	-	pF	

Note

• BiAs mode (between pin 3 and pin 1)

For technical questions, contact: ESDprotection@vishay.com
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Single-Line ESD-Protection in SOT-23

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ELECTRICAL CHARACTERISTICS GSOT04							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines	
Reverse working voltage	at I _R = 20 μA	V_{RWM}	4	-	-	V	
Reverse current	at V _R = 4 V	I _R	=	-	20	μA	
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	5	6.1	-	V	
Reverse clamping voltage	at I _{PP} = 1 A	V	=	7.5	9	V	
neverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	=	11.2	14.3	V	
Forward clamping voltage	at I _{PP} = 1 A	V _F	=	1	1.2	V	
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	VF	=	4.5	-	V	
0	at V _R = 0 V; f = 1 MHz	- C _D	=	310	450	pF	
Capacitance	at V _R = 2 V; f = 1 MHz	C _D	=	200	-	pF	

Note

• BiAs mode (between pin 3 and pin 1)

ELECTRICAL CHARACTERISTICS GSOT05							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	=	-	1	lines	
Reverse working voltage	at I _R = 10 μA	V_{RWM}	5	-	-	V	
Reverse current	at V _R = 5 V	I _R	=	-	10	μΑ	
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	6	6.8	-	V	
Reverse clamping voltage	at I _{PP} = 1 A	M	=	7	8.7	V	
neverse clamping voltage	at $I_{PP} = I_{PPM} = 30 \text{ A}$	V _C	-	12	16	V	
Forward clamping voltage	at I _{PP} = 1 A	V _F	=	1	1.2	V	
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	VF	=	4.5	-	V	
Capacitance	at V _R = 0 V; f = 1 MHz		=	260	350	pF	
Сараспапсе	at V _R = 2.5 V; f = 1 MHz	C _D	=	150		pF	

Note

• BiAs mode (between pin 3 and pin 1)

ELECTRICAL CHARACTERISTICS GSOT08						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse working voltage	at I _R = 5 μA	V_{RWM}	8	-	-	V
Reverse current	at V _R = 8 V	I _R	-	-	5	μA
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	9	10	-	V
- · · · · ·	at I _{PP} = 1 A	- V _C	-	10.7	13	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 18 A		-	15.2	19.2	V
Forward clamping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V
	at Ipp = IppM = 18 A		-	3	-	V
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	160	250	pF
	at V _R = 4 V; f = 1 MHz		-	80	-	pF

Note

• BiAs mode (between pin 3 and pin 1)

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GSOT03 to GSOT36

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Single-Line ESD-Protection in SOT-23



ELECTRICAL CHARACTERISTICS GSOT12						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse working voltage	at I _R = 1 μA	V _{RWM}	12	-	-	V
Reverse current	at V _R = 12 V	I _R	-	-	1	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	13.5	15	-	V
D	at I _{PP} = 1 A	V _C	=	15.4	18.7	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 12 A		-	21.2	26	V
Forward clamping voltage	at I _{PP} = 1 A	V _F	=	1	1.2	V
	at I _{PP} = I _{PPM} = 12 A		=	2.2	-	V
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	=	115	150	pF
	at V _R = 6 V; f = 1 MHz		-	50	-	pF

Note

• BiAs mode (between pin 3 and pin 1)

ELECTRICAL CHARACTERISTICS GSOT15						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse working voltage	at I _R = 1 μA	V_{RWM}	15	-	-	V
Reverse current	at V _R = 15 V	I _R	-	-	1	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	16.5	18	-	V
D	at I _{PP} = 1 A	- V _C	-	19.4	23.5	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 8 A		-	24.8	28.8	V
Forward alamping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 8 A		-	1.8	-	V
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	90	120	pF
	at V _R = 7.5 V; f = 1 MHz		-	35	-	pF

Note

• BiAs mode (between pin 3 and pin 1)

PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse working voltage	at I _R = 1 μA	V_{RWM}	24	-	-	V
Reverse current	at V _R = 24 V	I _R	-	-	1	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	27	30	-	V
Devenue elementar celtare	at I _{PP} = 1 A	W	-	34	41	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 5 A	V _C	-	41	47	V
Forward clamping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V
	at I _{PP} = I _{PPM} = 5 A		-	1.4	-	V
Capacitance	at V _R = 0 V; f = 1 MHz	- C _D	-	65	80	pF
	at V _R = 12 V; f = 1 MHz		-	20	-	рF

Note

• BiAs mode (between pin 3 and pin 1)



Single-Line ESD-Protection in SOT-23

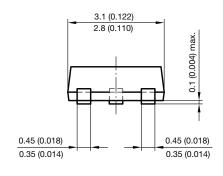
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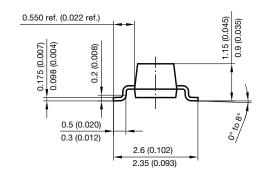
ELECTRICAL CHARACTERISTICS GSOT36						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse working voltage	at I _R = 1 μA	V _{RWM}	36	-	=	V
Reverse current	at V _R = 36 V	I _R	-	-	1	μΑ
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	39	43	-	V
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	49	60	V
neverse clamping voltage	at $I_{PP} = I_{PPM} = 3.5 \text{ A}$	V _C	-	59 7	71	V
Forward alamping voltage	at I _{PP} = 1 A	V _F	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 3.5 A		-	1.3	-	V
Canacitanas	at V _R = 0 V; f = 1 MHz	- C _D	-	52	65	pF
Capacitance	at V _R = 18 V; f = 1 MHz		-	12	=	pF

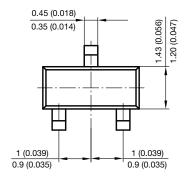
Note

• BiAs mode (between pin 3 and pin 1)

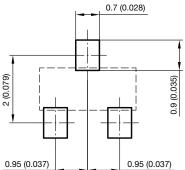
PACKAGE DIMENSIONS in millimeters (inches): SOT-23











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